Octal Bus Buffer

With 5V-Tolerant Inputs

The MC74LVX244 is an advanced high speed CMOS non-inverting 3-state octal bus buffer and has two active low output enables. It is also designed to work with 3-state memory address drivers, etc. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: $t_{PD} = 4.7 \text{ns}$ (Typ) at $V_{CC} = 3.3 \text{V}$
- Low Power Dissipation: $I_{CC} = 4\mu A$ (Max) at $T_A = 25$ °C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.8V$ (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V

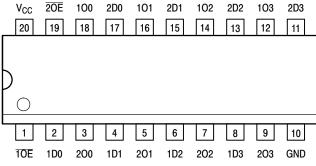


Figure 1. 20-Lead Pinout (Top View)

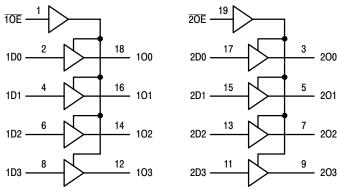


Figure 2. Logic Diagram

MC74LVX244



LOW-VOLTAGE CMOS



DW SUFFIX 20-LEAD SOIC PACKAGE CASE 751D-04



DT SUFFIX 20-LEAD TSSOP PACKAGE CASE 948E-02



M SUFFIX 20-LEAD SOIC EIAJ PACKAGE CASE 967-01

PIN NAMES

Pins	Function
nOE	Output Enable Inputs
1Dn, 2Dn	Data Inputs
1On, 2On	3–State Outputs

FUNCTION TABLE

INP	JTS	OUTPUTS
10E, 20E	1Dn, 2Dn	10n, 20n
L	L	L
L	Н	Н
Н	X	Z

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±75	mA
P _D	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C

^{*} Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	T _A = 25°C			T _A = - 40 to 85°C		
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OH} = -50\mu A$ $I_{OH} = -50\mu A$ $I_{OH} = -4mA$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OL} = 50\mu A$ $I_{OL} = 50\mu A$ $I_{OL} = 4mA$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I _{in}	Input Leakage Current	V _{in} = 5.5V or GND	3.6			±0.1		±1.0	μА
l _{OZ}	Maximum Three–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.25		±2.5	μА
I _{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			4.0		40.0	μА

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

					T _A = 25°C		$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay Input to Output	V _{CC} = 2.7V	$C_L = 15pF$ $C_L = 50pF$		6.1 8.6	11.4 14.9	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		4.7 7.2	7.1 10.6	1.0 1.0	8.5 12.0	
t _{PZL} , t _{PZH}	Output Enable Time to High and Low Level	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.1 9.6	13.8 17.3	1.0 1.0	16.5 20.0	ns
		$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		5.5 8.0	8.8 12.3	1.0 1.0	10.5 14.0	
t _{PLZ} , t _{PHZ}	Output Disable Time From High and Low Level	$V_{CC} = 2.7V$ $R_L = 1k\Omega$	C _L = 50pF		11.6	16.0	1.0	19.0	ns
		$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	C _L = 50pF		9.7	11.4	1.0	13.0	
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note NO TAG)	$V_{CC} = 2.7V$ $V_{CC} = 3.3 \pm 0.3V$	$C_L = 50pF$ $C_L = 50pF$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

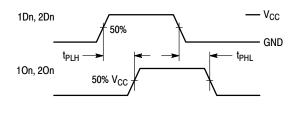
		T _A = 25°C		T _A = - 40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
C _{in}	Input Capacitance		4	10		10	pF
C _{out}	Maximum Three–State Output Capacitance		6				pF
C _{PD}	Power Dissipation Capacitance (Note NO TAG)		19				pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

SWITCHING WAVEFORMS



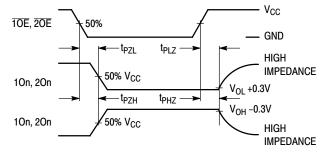
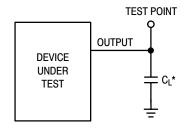


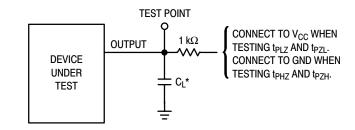
Figure 3.

Figure 4.

TEST CIRCUITS



^{*}Includes all probe and jig capacitance



*Includes all probe and jig capacitance

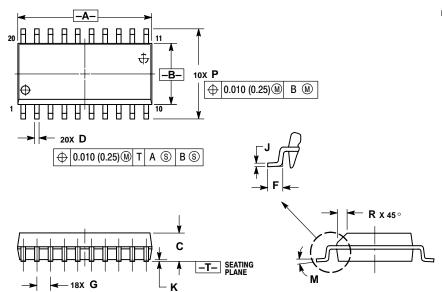
Figure 5. Propagation Delay Test Circuit

Figure 6. Three-State Test Circuit

OUTLINE DIMENSIONS

DW SUFFIX

PLASTIC SOIC PACKAGE CASE 751D-04 ISSUE E



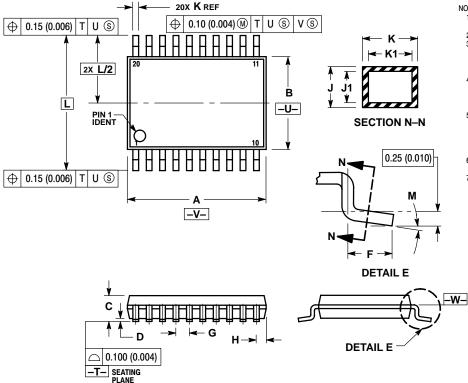
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.150 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	12.65	12.95	0.499	0.510
В	7.40	7.60	0.292	0.299
С	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27	BSC	0.050	BSC
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

OUTLINE DIMENSIONS

DT SUFFIX

PLASTIC TSSOP PACKAGE CASE 948E-02 ISSUE A



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
 - (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR
 - PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
- EXCESS OF THE R DIMENSION AT MAXIMUM MATERIAL CONDITION.

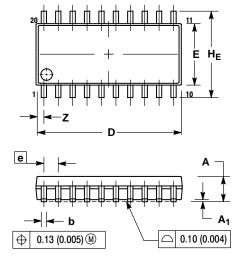
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

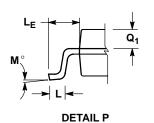
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

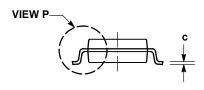
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252		
M	0°	8°	0°	8°	

OUTLINE DIMENSIONS

M SUFFIX PLASTIC SOIC EIAJ PACKAGE CASE 967-01 ISSUE O







- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 - PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
 PER SIDE.
 TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
 INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
 TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER
 RADIUS OR THE FOOT. MINIMUM SPACE
 BETWEEN PROTRUSIONS AND ADJACENT LEAD
 TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.81		0.032

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